# imall

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BC847BVN

COMPLEMENTARY PAIR SMALL SIGNAL SURFACE MOUNT TRANSISTOR

#### Features

- Epitaxial Die Construction
- Two Internally Isolated NPN/PNP Transistors in One Package
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

#### **Mechanical Data**

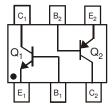
- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.003 grams (Approximate)



Top View



Bottom View



Device Schematic Top View

#### Ordering Information (Notes 4 & 5)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
BC847BVN-7	AEC-Q101	KAW	7	8	3,000
BC847BVNQ-7	Automotive	KAW	7	8	3,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

SOT563

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

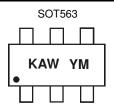
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_compliance\_definitions/.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

#### **Marking Information**

Notes:



 $\begin{array}{l} \mathsf{KAW} = \mathsf{Product Type Marking Code} \\ \mathsf{YM} = \mathsf{Date Code Marking} \\ \mathsf{Y} = \mathsf{Year} \ (\mathsf{ex: Y} = 2011) \\ \mathsf{M} = \mathsf{Month} \ (\mathsf{ex: 9} = \mathsf{September}) \end{array}$ 

Date Code Ke	у											
Year	2010	201	1	2012	20	013	2014	2	2015	2016		2017
Code	Х	Y	,	Z		A	В		С	D		E
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# Maximum Ratings: NPN, BC847B Type (Q<sub>1</sub>) (@T<sub>A</sub> = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	45	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Collector Current	Ιc	100	mA
Peak Collector Current	ICM	200	mA
Peak Emitter Current	I <sub>EM</sub>	200	mA

# Maximum Ratings: PNP, BC857B Type (Q<sub>2</sub>) (@T<sub>A</sub> = +25 °C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-45	V
Emitter-Base Voltage	V <sub>EBO</sub>	-6	V
Collector Current	lc	-100	mA
Peak Collector Current	ICM	-200	mA
Peak Emitter Current	I <sub>EM</sub>	-200	mA

#### Thermal Characteristics – Total Device (@T<sub>A</sub> = +25 °C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6) Total Device	PD	150	mW
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>0JA</sub>	833	°C/W
Operating and Storage Temperature Range	TJ, T <sub>STG</sub>	-65 to +150	°C

Note: 6. For a device surface mounted on minimum recommended pad layout FR-4 PCB with single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

#### Electrical Characteristics: NPN, BC847B Type (Q1) (@TA = +25 °C unless otherwise specified.)

Characteristic (Note 7)	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	50	-	—	V	$I_{C} = 100 \mu A, I_{B} = 0$
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	45			V	$I_{\rm C} = 10 {\rm mA}, \ I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6	_		V	$I_E = 100 \mu A, I_C = 0$
DC Current Gain	h <sub>FE</sub>	200	290	450	_	$V_{CE} = 5.0V, I_{C} = 2.0mA$
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>		90 200	250 600	mV	$I_{C} = 10mA$ , $I_{B} = 0.5mA$ $I_{C} = 100mA$ , $I_{B} = 5.0mA$
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>		700 900		mV	$I_{C} = 10mA$ , $I_{B} = 0.5mA$ $I_{C} = 100mA$ , $I_{B} = 5.0mA$
Base-Emitter Voltage	$V_{\text{BE(on)}}$	580 —	660 —	700 720	mV	$V_{CE} = 5.0V, I_C = 2.0mA$ $V_{CE} = 5.0V, I_C = 10mA$
Collector-Cutoff Current	I <sub>CBO</sub>			15 5.0	nA μA	V <sub>CB</sub> = 30V V <sub>CB</sub> = 30V, T <sub>A</sub> = +150℃
Gain Bandwidth Product	fT	100	300		MHz	$V_{CE} = 5.0V, I_C = 10mA, f = 100MHz$
Collector-Base Capacitance	Ссво	_	3.5	6.0	pF	$V_{CB} = 10V, f = 1.0MHz$

Note: 7. Short duration pulse test used to minimize self-heating effect.



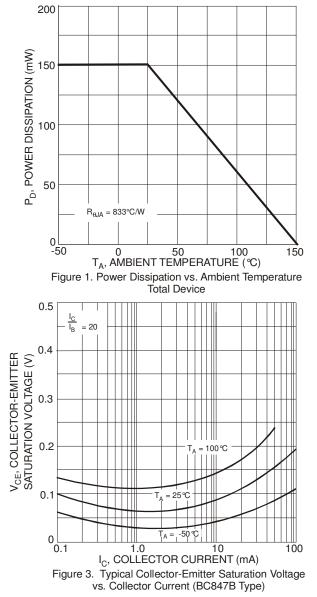
#### BC847BVN

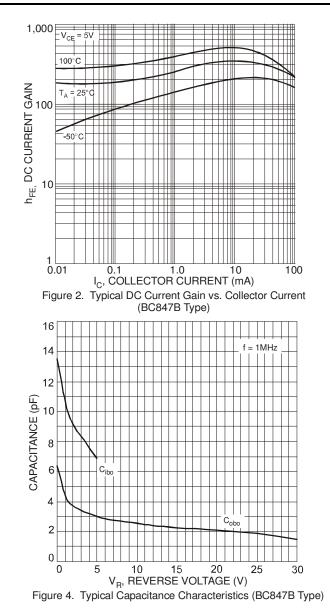
# Electrical Characteristics: PNP, BC857B Type (Q<sub>2</sub>) (@T<sub>A</sub> = +25 °C unless otherwise specified.)

Characteristic (Note 8)	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-50	_		V	$I_{C} = -100 \mu A, I_{B} = 0$
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	-45	—		V	$I_{\rm C} = -10 {\rm mA}, \ I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-6	_		V	$I_{E} = -100 \mu A, I_{C} = 0$
DC Current Gain	h <sub>FE</sub>	220	290	475	_	$V_{CE} = -5.0V, I_{C} = -2.0mA$
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>		-75 -250	-300 -650	mV	$I_{C} = -10mA$ , $I_{B} = -0.5mA$ $I_{C} = -100mA$ , $I_{B} = -5.0mA$
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>		-700 -850	 -950	mV	I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA I <sub>C</sub> = -100mA, I <sub>B</sub> = -5.0mA
Base-Emitter Voltage	V <sub>BE(on)</sub>	-600	-650 —	-750 -820	mV	$V_{CE} = -5.0V, I_C = -2.0mA$ $V_{CE} = -5.0V, I_C = -10mA$
Collector-Cutoff Current	I <sub>CBO</sub>		_	-15 -4.0	nA μA	V <sub>CB</sub> = -30V V <sub>CB</sub> = -30V, T <sub>A</sub> = +150 °C
Gain Bandwidth Product	f⊤	100	200	_	MHz	$V_{CE} = -5.0V, I_{C} = -10mA,$ f = 100MHz
Collector-Base Capacitance	Ссво	_	3	4.5	pF	V <sub>CB</sub> = -10V, f = 1.0MHz

Note: 8. Short duration pulse test used to minimize self-heating effect.

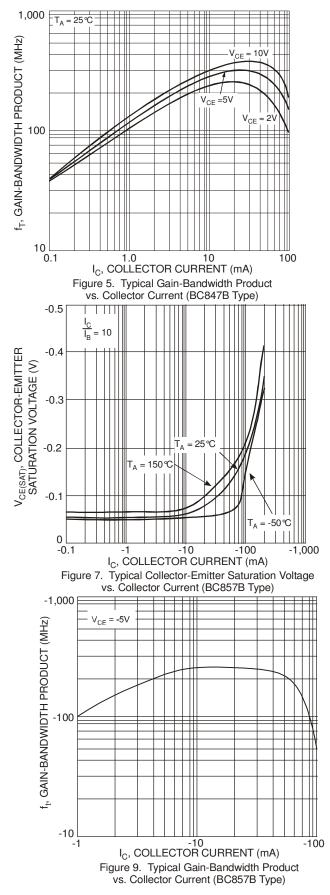
#### **Thermal Characteristics – Total Device**

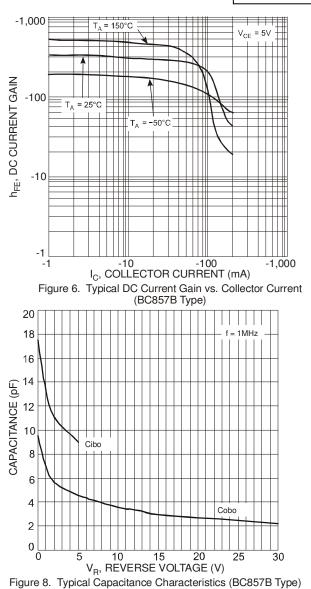






## BC847BVN

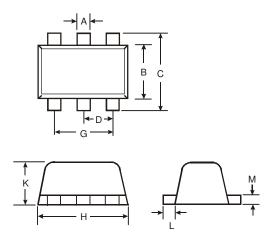






#### **Package Outline Dimensions**

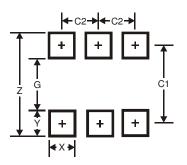
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT563							
Dim	Min	Max	Тур					
Α	0.15	0.30	0.20					
В	1.10	1.25	1.20					
С	1.55	1.70	1.60					
D	-	-	0.50					
G	0.90	1.10	1.00					
Н	1.50	1.70	1.60					
Κ	0.55	0.60	0.60					
L	0.10	0.30	0.20					
М	0.10	0.18	0.11					
All	Dimens	sions in	mm					

#### **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Y	0.5
C1	1.7
C2	0.5



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